

K. Memory (Design & Process Technology) 분과

2017년 2월 15일 (수), 15:25-17:10
Room B (토파즈, 2층)

[WB4-K] Understanding Resistance Switching Phenomena

좌장: 백인규(삼성전자), 권용우(홍익대학교)

WB4-K-1 15:25-15:40	Anomalous Quantum Conductance in Ta₂O₅ and HfO₂ Resistance Switching Memory Tae Hyung Park ¹ , Hae Jin Kim ¹ , Soo Gil Kim ² , Byung Joon Choi ³ , and Cheol Seong Hwang ¹ <i>¹Department of Materials Science and Engineering and Inter-University Semiconductor Research Center, Seoul National University, ²SK Hynix Inc., ³Department of Materials Science and Engineering, Seoul National University of Science and Technology</i>
WB4-K-2 15:40-16:10	[초청] Analog Resistive Switching Devices for Artificial Synapse in Neuromorphic Systems Hyung Jun Kim, Hong Zheng, Paul Yang, and Tae-Sik Yoon <i>Department of Materials Science and Engineering, Myongji University</i>
WB4-K-3 16:10-16:25	A Study of the Transition between the Non-Polar and Bipolar Resistance Switching Mechanisms in the TiN/TiO₂/Al Memory Xing Long Shao ¹ , Kyung Min Kim ² , Kyung Jean Yoon ¹ , Seul Ji Song ¹ , Jung Ho Yoon ¹ , Hae Jin Kim ¹ , Tae Hyung Park ¹ , Dae Eun Kwon ¹ , Young Jae Kwon ¹ , Yu Min Kim ¹ , Nuo Xu ¹ , Xi Wen Hu ³ , Jin Shi Zhao ³ , and Cheol Seong Hwang ¹ <i>¹Department of Materials Science and Engineering and Inter-University Semiconductor Research Center, Seoul National University, ²Hewlett-Packard Laboratories, Hewlett-Packard Company, ³School of Electronics Information Engineering, Tianjin Key Laboratory</i>
WB4-K-4 16:25-16:40	Understanding of Relaxation Characteristic in Filament-type ReRAM 박용택, 이재연, 하태정, 박우영, 김경완, 김수길 <i>SK Hynix R&D 부문</i>
WB4-K-5 16:40-16:55	A Study on Switching Fail Mechanism of Ta/HfO₂ for ReRAM Woo Young Park ¹ , Tae Jung Ha ¹ , Jae Yeon Lee ¹ , Yong Taek Park ¹ , Su Hyun Lee ¹ , Tae One Youn ² , Min Ki Choi ² , Soo Gil Kim ¹ , and Hyeong Soo Kim ¹ <i>¹Advanced Cell Research Team, R&D Division, SK Hynix Semiconductor Inc., ²AT Team, R&D Division, SK Hynix Semiconductor Inc.</i>
WB4-K-6 16:55-17:10	Filament Growth Controlled Memristive Switching Memory Device via Nanocone Patterning Byoung Kuk You, Tae Jin Kim, Jong Min Kim, Daniel J. Joe, and Keon Jae Lee <i>Department of Material Science and Engineering, KAIST</i>